

ABSTRACT OF THE DISCLOSURE

An aspect of the present invention includes a first
conductive type semiconductor region formed in a
5 semiconductor substrate, a gate electrode formed on the first
conductive type semiconductor region, a channel region formed
immediately below the gate electrode in the first conductive
type semiconductor region, and a second conductive type first
diffusion layers constituting source/drain regions formed
10 at opposite sides of the channel region in the first
conductive type semiconductor region, the gate electrode
being formed of polycrystalline silicon-germanium, in which
the germanium concentration of at least one of the source
side and the drain side is higher than that of the central
15 portion.